

CONTENTS

	Page
ACKNOWLEDGEMENTS	
ABSTRACT	
CHAPTER 1	01
INTRODUCTION	01
1.1 General Background	01
1.2 The Sun and Solar Radiation	02
1.3 Types of Solar Cells	04
1.3.1 Single-crystalline and polycrystalline silicon	04
1.3.2 Group III-V technologies	06
1.3.2.1 Gallium arsenide	06
1.3.2.2 Indium phosphide	07
1.3.3 Thin film solar cells	07
1.3.3.1 Amorphous silicon (a-Si:H)	08
1.3.3.2 Cadmium telluride (CdTe)	09
1.3.3.3 Copper indium diselenide (CuInSe ₂)	10
1.4 Basis and Scope of this Work	11
1.4.1 Motivation	11
1.4.2 Definition of research problem	11
1.4.3 Objective of the research	12
1.5 Thesis Organization	13
REFERENCES	14
CHAPTER 2	17
THEORETICAL BACKGROUND: THIN FILM PHOTOVOLTAICS	17
2.1 Introduction	17
2.2 Material Properties of CuInSe ₂	17
2.2.1 Crystallographic structure of chalcopyrite compounds	17
2.2.2 Phase diagram of Cu-In-Se	19
2.2.3 Optical properties	21
2.2.4 Defect structure and electrical properties	23
2.3 Processing Technique for Chalcopyrite Thin Films	27
2.4 Diffusion Processes and Reaction Kinetics of CuInSe ₂	31
2.5 Design and Fabrication of CIS Based Solar Cell Devices	33
2.5.1 Introduction	33

2.5.2	Structure of the heterojunction solar cell	34
2.5.3	Module fabrication process	36
REFERENCES		38
CHAPTER 3		44
FUNDAMENTAL PRINCIPLES OF SOLAR CELL DEVICES		44
3.1	Introduction	44
3.2	Outline of Solar Cell Development	44
3.3	p- n Junction Diodes	45
3.3.1	Introduction	45
3.3.2	Electrostatic analysis p-n junctions	46
3.3.3	Calculation of the contact potential (built in voltage)	48
3.3.4	Abrupt p-n junction	50
3.3.5	Current–voltage characteristics	52
3.3.6	Recombination/generation in the depletion region	55
	3.3.6.1 Band-to-band recombination	56
	3.3.6.2 Shockley-Hall-Read recombination	57
	3.3.7 The illuminated I-V curve	59
3.4	Solar Cell Output Parameters	61
3.5	Efficiency Limits and Losses	62
	3.5.1 Short-circuit current	62
	3.5.2 Open-circuit voltage and efficiency of solar cell	64
	3.5.3 Fill factor(FF)	65
3.6	Voltage Dependence of the Light Generated Currents	67
REFERENCES		68
CHAPTER 4		70
EXPERIMENTAL PROCEDURES		70
4.1	Introduction	70
4.2	Substrate Preparation	70
4.3	Molybdenum Deposition	71
4.4	Absorber Formation	72
	4.4.1 Introduction	72
	4.4.2 Three-source evaporation system	72
	4.4.3 Growth procedure	76
	4.4.3.1 Preparation of selenium-containing precursors	76
	4.4.3.2 Selenization processes	77

	4.4.3.3	Post-sulfurization of CuInSe_2	78
4.5		Device Fabrication	78
	4.5.1	CdS buffer layer deposition	78
	4.5.2	ZnO window layer deposition	80
	4.5.3	Ni/Al front contact deposition	81
4.6		Film Characterization Techniques	81
	4.6.1	Introduction	81
	4.6.2	Structural analysis	82
	4.6.2.1	Introduction	82
	4.6.2.2	Determination of thickness	82
	4.6.2.3	Scanning electron microscopy (SEM) and energy dispersive x-ray spectroscopy(EDS)	83
	4.6.2.4	X-Ray fluorescence (XRF)	83
	4.6.2.5	X-Ray diffraction (XRD)	84
	4.6.3	Optical properties	85
	4.6.3.1	UV-VIS-NIR spectroscopy	86
	4.6.3.2	Photoluminescence	87
	4.6.4	Device characterization	88
REFERENCES			89
CHAPTER 5			90
RESULTS AND DISCUSSION			90
5.1		Introduction	90
5.2		Deposition of CuInSe_2 Absorber Films	91
	5.2.1	Introduction	91
	5.2.2	Structural features of Cu-In-Se precursors	91
	5.2.3	Structural features of CuInSe_2 thin films	96
	5.2.4	In-depth compositional uniformity of selenized films	98
5.3		Preparation of $\text{CuIn}(\text{Se}, \text{S})_2$ Thin Films	100
	5.3.1	Introduction	100
	5.3.2	Structural features of $\text{CuIn}(\text{Se}, \text{S})_2$ thin films	100
	5.3.3	In-depth composition uniformity of sulfurized films	103
5.4		Formation of $\text{Cu}(\text{In}, \text{Ga})\text{Se}_2$ Thin Films	105
	5.4.1	Introduction	105
	5.4.2	Influence of the stacking order on structural features of Cu-In-Ga-Se precursors	106
	5.4.3	Relationship between precursor structure and material properties of the $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2$ thin films	112
	5.4.4	Influence of selenization temperature on crystalline quality of absorbers	117
	5.4.5	Influence of GaSe deposition temperature on the structural features and in-depth compositional uniformity of $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2$ thin films	124
	5.4.5.1	Introduction	124
	5.4.5.2	Structural features of films	125

5.4.5.3	In-depth compositional uniformity of samples	132
5.4.6	The influence of gallium concentration on structural and optical properties of Cu(In,Ga)Se ₂	138
5.4.6.1	Introduction	138
5.4.6.2	Influence of Ga concentration on structural features of Cu(In,Ga)Se ₂	139
5.4.6.3	Optical properties of Cu(In,Ga)Se ₂ as function of Ga content	145
5.5	Device Fabrication and Analysis	150
5.5.1	Introduction	150
5.5.2	Material quality of CdS and ZnO	150
5.5.3	Device analysis	154
REFERENCES		160
CHAPTER 6		161
CONCLUSIONS		161

